

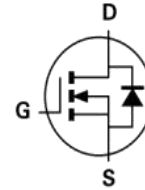


LT80N04AD/U

N-Channel Enhancement Mode MOSFET

MAIN CHARACTERISTICS

I_D	80A
V_{DSS}	40V
$R_{DS(on)-typ}$ (@ $V_{GS}=10V$)	5.5m Ω

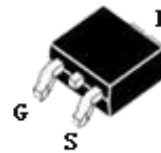


FEATURES

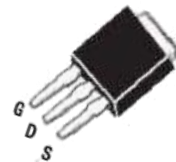
- Adopt advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

APPLICATIONS

- Battery protection
- Load switch
- Uninterruptible power supply



TO-252



TO-251

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275°C maximum, 10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LT80N04AD	TO-252	LT80N04AD	Tape
LT80N04AU	TO-251	LT80N04AU	Tape



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Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continue Drain Current	I_D	80	A
Pulsed Drain Current (Note1)	I_{DM}	350	A
Power Dissipation	P_D	80	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	750	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.88	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	BV_{DSS}	40	-	-	V
Drain-Source Leakage Current	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	1.1	-	2.4	V
Drain-Source On-State Resistance	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	$R_{DS(on)}$	-	5.5	7	m Ω
	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	$R_{DS(on)}$	-	8	12	m Ω
Forward Transconductance	$V_{DS} = 10 \text{ V}, I_D = 20 \text{ A}$	gfs	15	-	-	S
Input Capacitance	$V_{DS}=20\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$	C_{iss}	-	2662	3200	pF
Output Capacitance		C_{oss}	-	322	-	pF
Reverse Transfer Capacitance		C_{rss}	-	246	-	pF
Turn-on Delay Time(Note2)	$V_{DD}=20\text{V}, V_{GS}=10\text{V}, R_G=3 \Omega, R_L=1 \Omega$	$t_{d(ON)}$	-	12	-	ns
Rise Time(Note2)		t_r	-	11	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	39	-	ns
Fall Time(Note2)		t_f	-	12	-	ns
Total Gate Charge(Note2)	$V_{DS}=20\text{V}, V_{GS}=10\text{V}, I_D=20\text{A}$	Q_G	-	54.3	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	6.9	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	14.5	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	80	A
Drain-Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=10\text{A}, T_J=25^\circ\text{C}$	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	$T_J = 25^\circ\text{C}, I_F = 20\text{A}$ $di/dt = 100 \text{ A}/\mu\text{s}$	trr	-	-	45	ns
Reverse Recovery Charge(Note2)		Qrr	-	-	50	nC

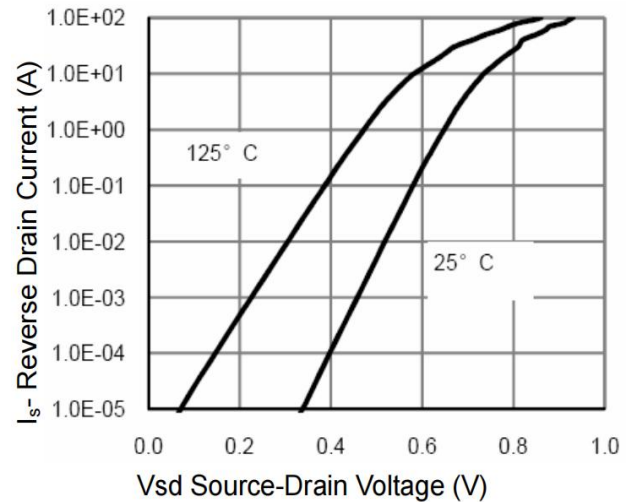
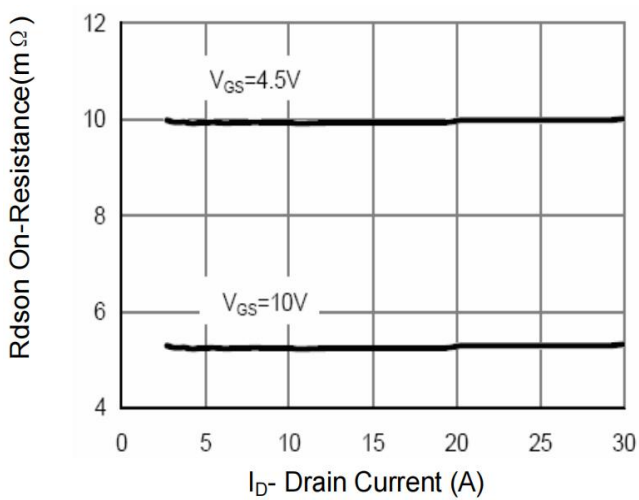
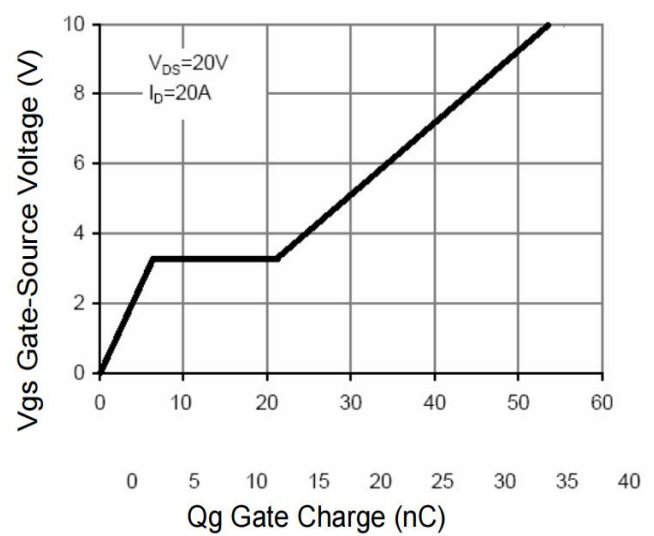
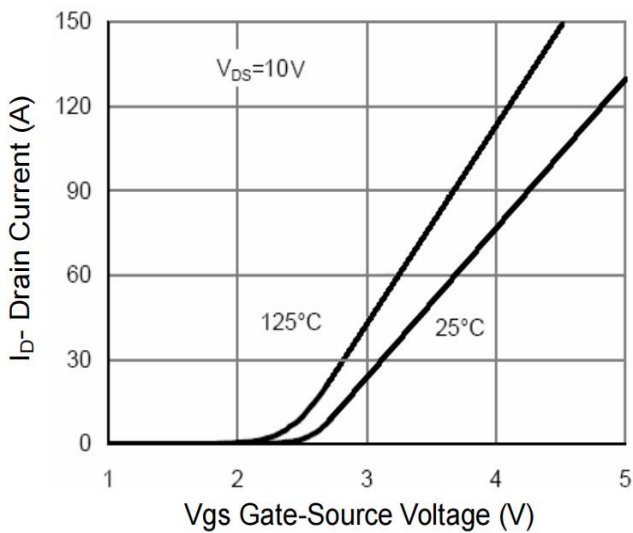
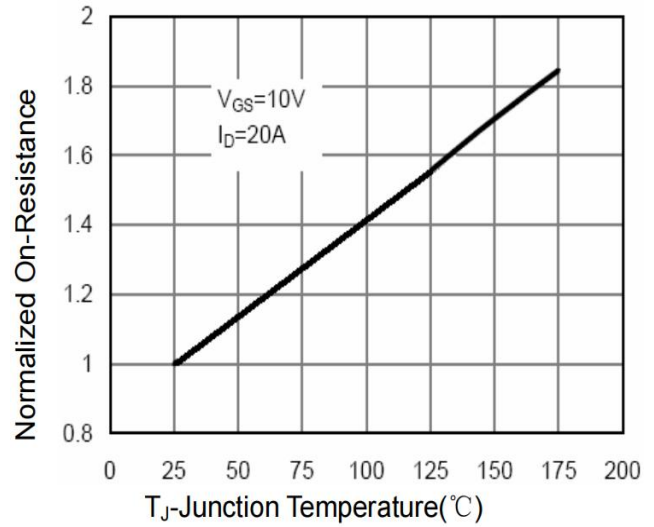
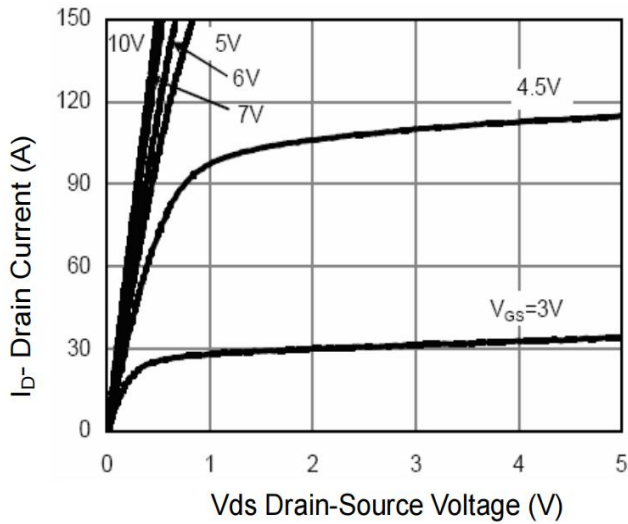
Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle



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RATINGS AND CHARACTERISTIC CURVES

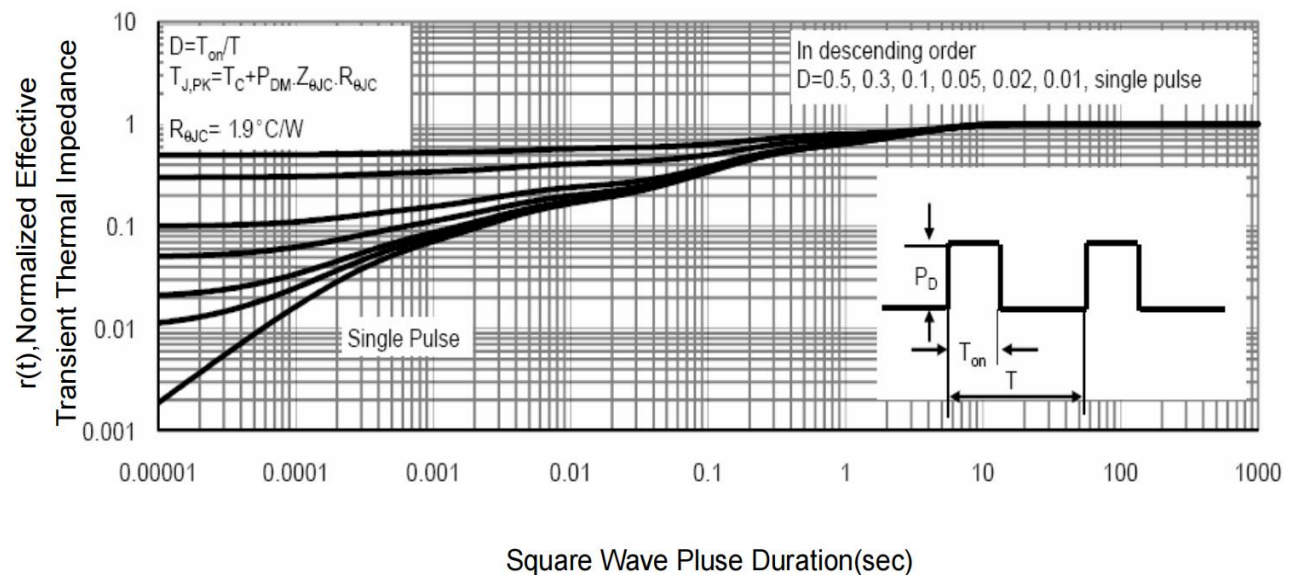
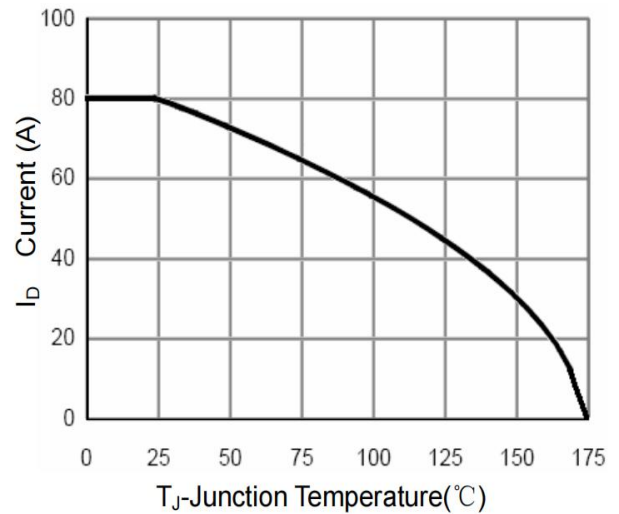
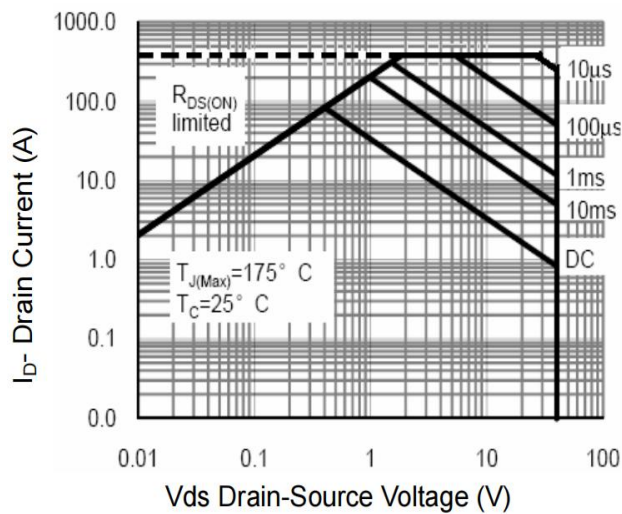
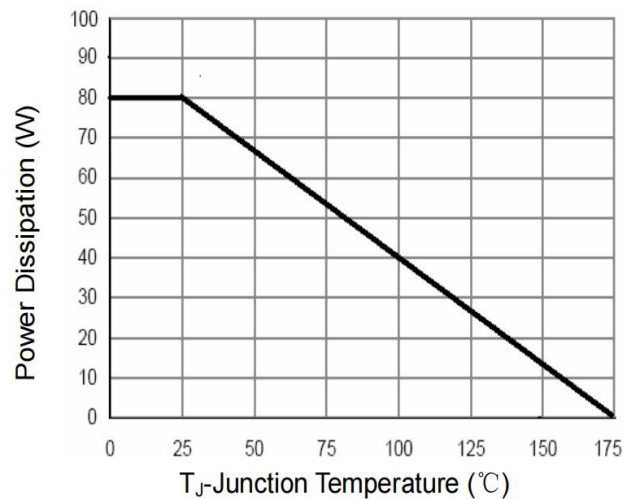
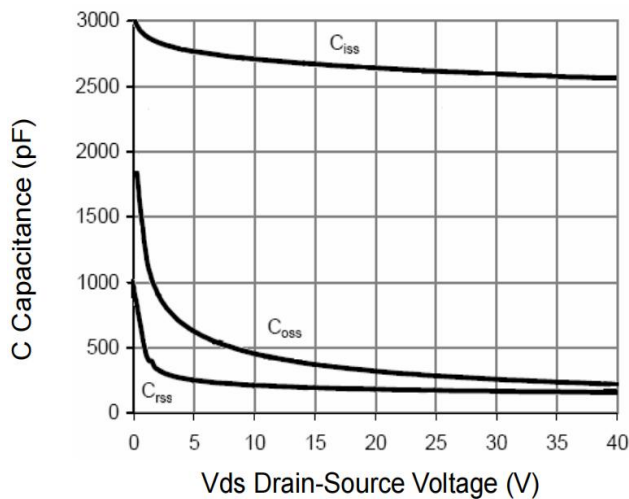




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RATINGS AND CHARACTERISTIC CURVES



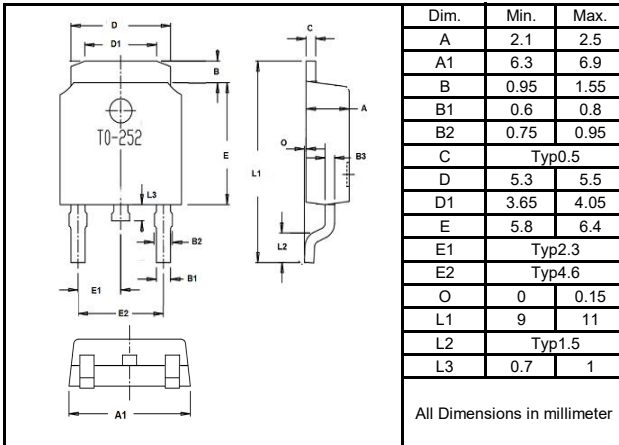


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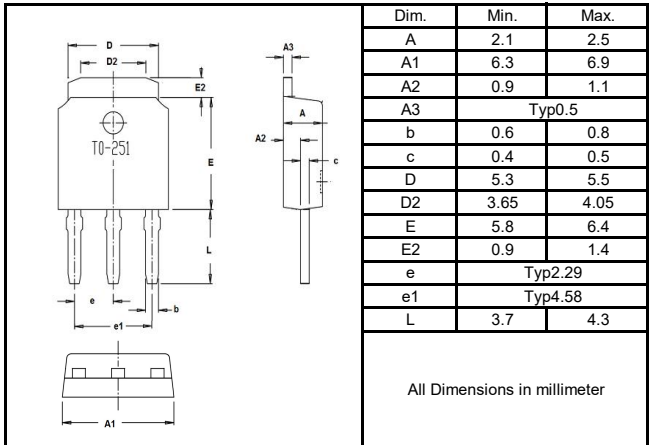
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Package Outline Dimensions millimeters

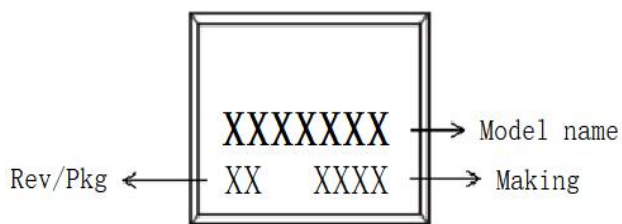
T0-252



T0-251



Marking on the body



MAKING:

X X XX

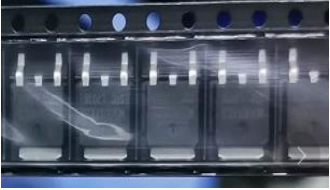
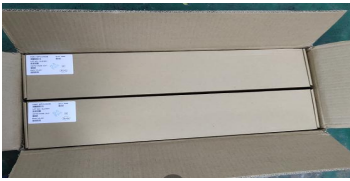
Assembly code (e.g : AB,CD,.....)

month-code (WW: 1-1, 10-A...)

Year-code

(Y: Last digit of year & A:2012,B:2013...)

packing instruction

PKG	最小包装	内盒	外箱
TO-252			
	2500pcs/盘	5000pcs/盒	25000pcs/箱
TO-251			
	80pcs/管	4000pcs/盒	24000pcs/箱

Notice

All product,product specifications and data are subject to change without notice to improve.The right to explain is owned by LINGXUN electronics

company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying poer exceeding normal rated

poer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliabilitv

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.